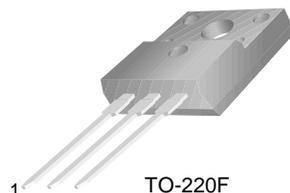


KSD1408

Power Amplifier Applications

- Complement to KSB1017



TO-220F
1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	4	A
I_B	Base Current	0.4	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 50\text{mA}, I_B = 0$	80			V
I_{CBO}	Collector Cut-off Current	$V_{CB} = 80\text{V}, I_E = 0$			30	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5\text{V}, I_C = 0$			100	μA
h_{FE1} h_{FE2}	DC Current Gain	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}$ $V_{CE} = 5\text{V}, I_C = 3\text{A}$	40 15	50	240	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 3\text{A}, I_B = 0.3\text{A}$		0.45	1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 5\text{V}, I_C = 3\text{A}$		1	1.5	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 5\text{V}, I_C = 0.5\text{A}$		8		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		90		pF

h_{FE1} Classification

Classification	R	O	Y
h_{FE1}	40 ~ 80	70 ~ 140	120 ~ 240

Typical Characteristics

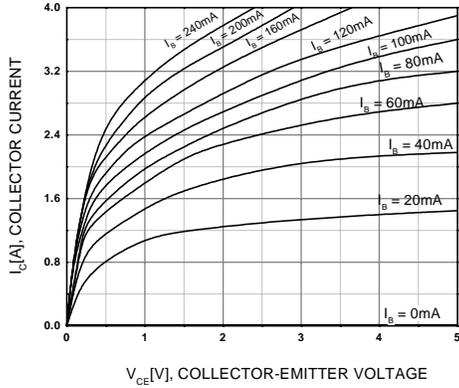


Figure 1. Static Characteristic

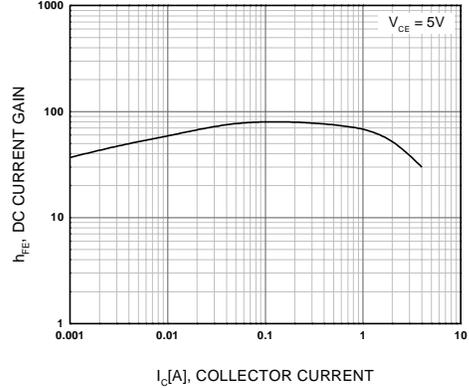


Figure 2. DC current Gain

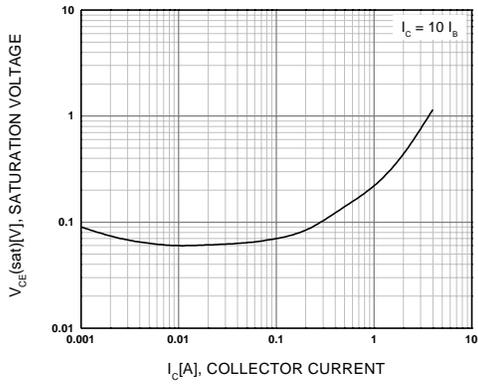


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

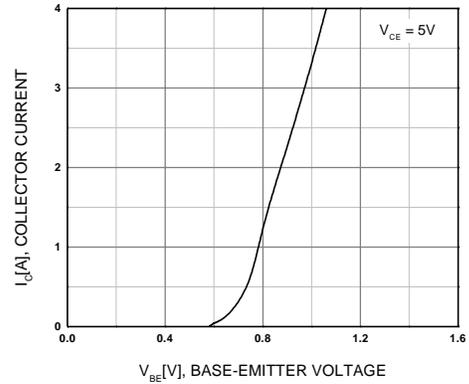


Figure 4. Collector Output Capacitance

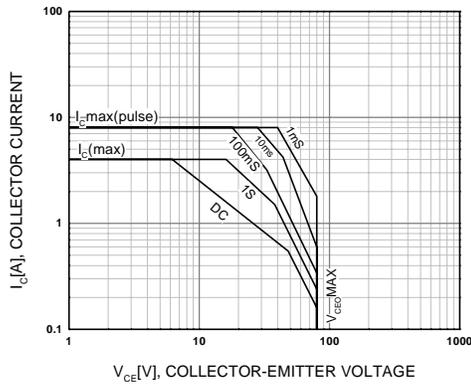


Figure 5. Safe Operating Area

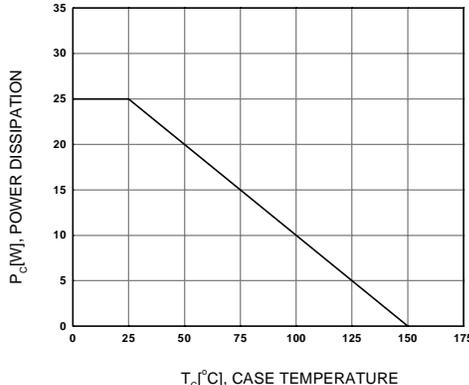
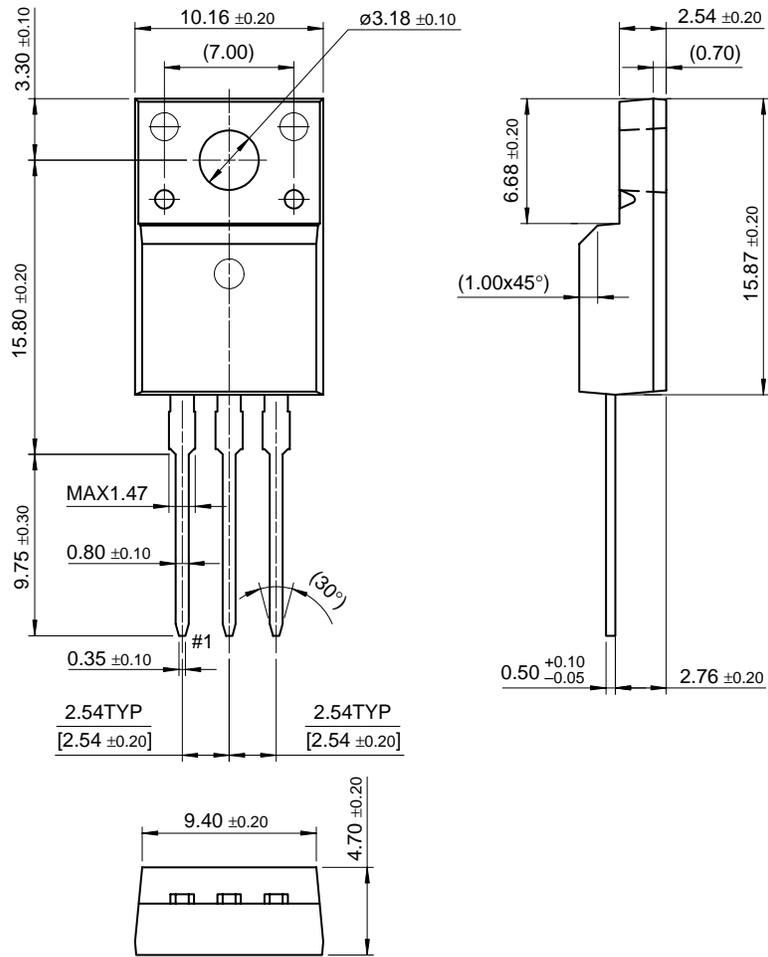


Figure 6. Power Derating

Package Dimensions

KSD1408

TO-220F



Dimensions in Millimeters

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KSD1408

NPN Epitaxial Silicon Transistor

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Features

- Complement to KSB1017

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Applications

Power Amplifier

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSD1408GTU	Full Production	\$0.336	TO-220F	3	RAIL
KSD1408YTU	Full Production	\$0.336	TO-220F	3	RAIL
KSD1408OTU	Full Production	\$0.336	TO-220F	3	RAIL

* 1,000 piece Budgetary Pricing

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